EMG3 / UMG3N / FMG3A

NPN 100mA 50V Complex Digital Transistors (Bias Resistor Built-in Transistors)

Parameter	Tr1 and Tr2
V _{CEO}	50V
I _{C(MAX.)}	100mA
R ₁	4.7k Ω

Features

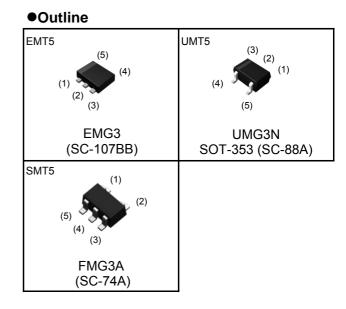
- 1) Built-In Biasing Resistors.
- 2) Two DTC143T chips in one package.
- 3) Emitter-common type.
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 5) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 6) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 7) Lead Free/RoHS Compliant.

Application

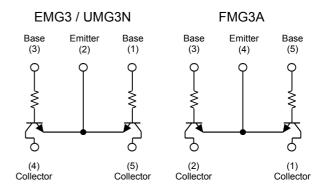
Inverter circuit, Interface circuit, Driver circuit

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMG3	EMT5	1616	T2R	180	8	8,000	G3
UMG3N	UMT5	2021	TR	180	8	3,000	G3
FMG3A	SMT5	2928	T148	180	8	3,000	G3



Inner circuit



Datasheet

•Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter		Symbol	Values	Unit
Collector-base voltage		V _{CBO}	50	V
Collector-emitter voltage		V _{CEO}	50	V
Emitter-base voltage		V _{EBO}	5	V
Collector current		I _{C(MAX.)} *1	100	mA
Power dissipation	EMG3 / UMG3N	n *2	150 (Total) ^{*3}	mW
	FMG3A	$- P_{D}^{*2}$	300 (Total) ^{*4}	mW
Junction temperature		Tj	150	°C
Range of storage temperature		T _{stg}	−55 to +150	°C

•Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV_{CBO}	I _C = 50μA	50	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	I _E = 50μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C / I _B = 5mA / 0.25mA	-	-	0.15	V
DC current gain	h _{FE}	V_{CE} = 5V , I _C = 1mA ,	100	250	600	-
Input resistance	R ₁	-	3.5	4.7	5.9	kΩ
Transition frequency	f _T *1	V _{CE} = 10V, I _E = –5mA, f = 100MHz	-	250	-	MHz

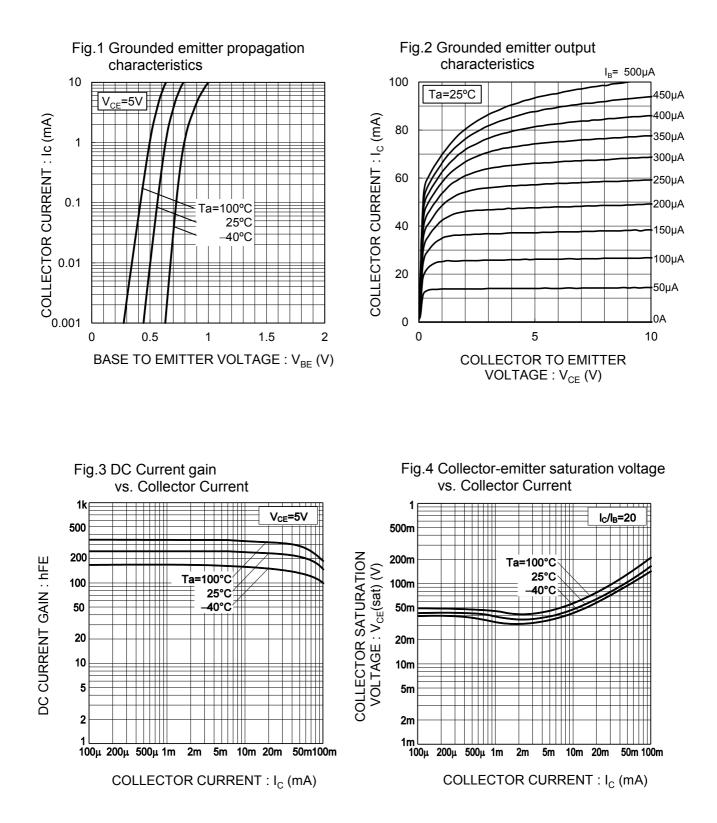
*1 Characteristics of built-in transistor

*2 Each terminal mounted on a reference footprint

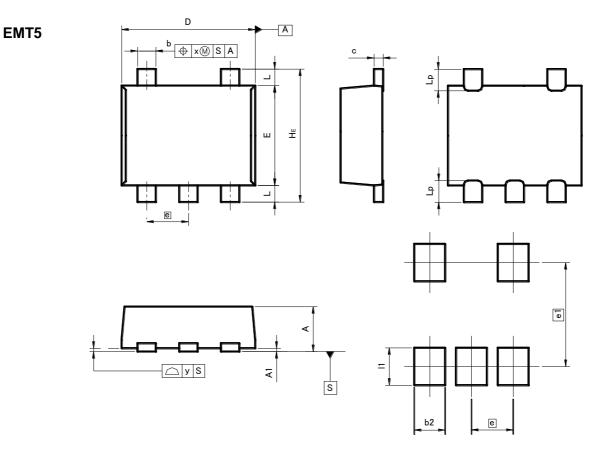
*3 120mW per element must not be exceeded.

*4 200mW per element must not be exceeded.

•Electrical characteristic curves(Ta = 25°C)



•Dimensions (Unit : mm)



Patterm of terminal position areas

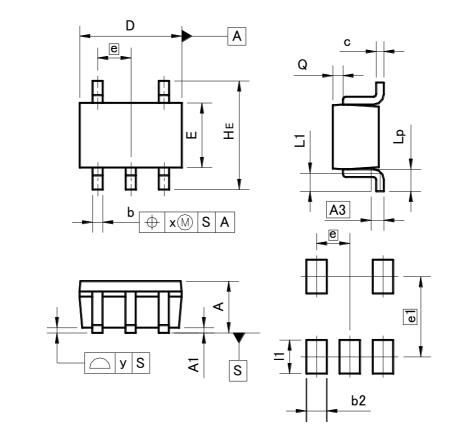
DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
A1	0.00	0.10	0	0.004	
А	0.45	0.55	0.018	0.022	
b	0.17	0.27	0.007	0.011	
с	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
E	1.10	1.30	0.043	0.051	
е	0.5	50	0.02		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	-	0.35	_	0.014	
x	-	0.10	_	0.004	
У	-	0.10	_	0.004	

DIM	MILIMETERS		INC	HES	
DIN	MIN	MAX	MIN	MAX	
e1	1.25		0.049		
b2	-	- 0.37		0.015	
1	_	0.45	-	0.018	

Dimension in mm/inches

•Dimensions (Unit : mm)

UMT5



Patterm of terminal position areas

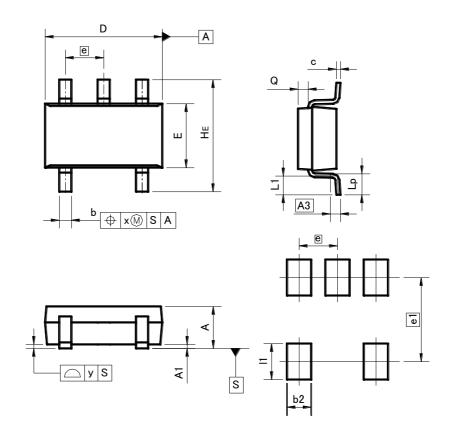
DIM	MILIM	MILIMETERS		HES	
DIM	MIN	MAX	MIN	MAX	
А	0.80	1.00	0.031	0.039	
A1	0.00	0.10	0	0.004	
A3	0.3	25	0.0	D1	
b	0.15	0.30	0.006	0.012	
с	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
E	1.15	1.35	0.045	0.053	
е	0.	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
x	_	0.10	_	0.004	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	1.55		0.06		
b2	-	- 0.40		0.016	
1	-	0.65	-	0.026	

Dimension in mm/inches

•Dimensions (Unit : mm)

SMT5



Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
А	1.00	1.30	-	0.051	
A1	0.00	0.10	0	0.004	
A3	0.3	25	0.0	D1	
b	0.25	0.40	0.01	0.016	
с	0.09	0.25	0.004	0.01	
D	2.80	3.00	0.11	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.04		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20	_	0.008	
у	_	0.10	-	0.004	

DIM	MILIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
e1	2.10		0.08		
b2		0.60	_	0.024	
1	-	0.90	-	0.035	

Dimension in mm/inches

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